## 1-, 2- and 4-Channel Low Capacitance ESD Protection Arrays

### **Features**

- 1, 2 and 4 channels of ESD protection
- Provides ESD protection to IEC61000-4-2 Level 4
  - 8kV contact discharge
  - 15kV air discharge
- Low channel input capacitance of 0.85pF typical
- Minimal capacitance change with temperature and voltage
- Channel input capacitance matching of 0.02pF typical is ideal for differential signals
- Mutual capacitance between signal pin and adjacent signal pin - 0.11pF typical
- Zener diode protects supply rail and eliminates the need for external by-pass capacitors
- Each I/O pin can withstand over 1000 ESD strikes
- Available in SOT and MSOP lead-free packages

## **Applications**

- USB2.0 ports at 480Mbps in desktop PCs, notebooks and peripherals
- IEEE1394 Firewire® ports at 400Mbps / 800Mbps
- DVI ports, HDMI ports in notebooks, set top boxes, digital TVs, LCD displays
- Serial ATA ports in desktop PCs and hard disk drives
- PCI Express ports
- General purpose high-speed data line ESD protection

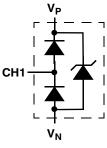
### **Product Description**

The CM1213A family of diode arrays has been designed to provide ESD protection for electronic components or sub-systems requiring capacitive loading. These devices are ideal for protecting systems with high data and clock rates or for circuits requiring low capacitive loading. Each ESD channel consists of a pair of diodes in series which steer the positive or negative ESD current pulse to either the positive  $(V_P)$  or negative  $(V_N)$  supply rail. A Zener diode is embedded between V<sub>P</sub> and V<sub>N</sub>, offering two advantages. First, it protects the V<sub>CC</sub> rail against ESD strikes, and second, it eliminates the need for a bypass capacitor that would otherwise be needed for absorbing positive ESD strikes to ground. The CM1213A will protect against ESD pulses up to ±8kV per the IEC 61000-4-2 standard and using the MIL-STD-883D (Method 3015) specification for Human Body Model (HBM) ESD, all pins are protected from contact discharges of greater than ±15kV.

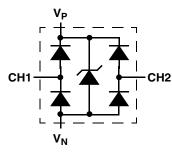
These devices are particularly well-suited for protecting systems using high-speed ports such as USB 2.0, IEEE1394 (Firewire®, iLink $^{TM}$ ), Serial ATA, DVI, HDMI and corresponding ports in removable storage, digital camcorders, DVD-RW drives and other applications where extremely low loading capacitance with ESD protection are required in a small package footprint.

The CM1213A family of devices is available with leadfree finishing.

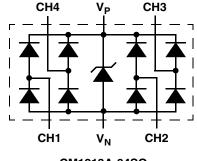
#### **Electrical Schematics**



CM1213A-01SO



CM1213A-02SO CM1213A-02SR



CM1213A-04SO CM1213A-04MR

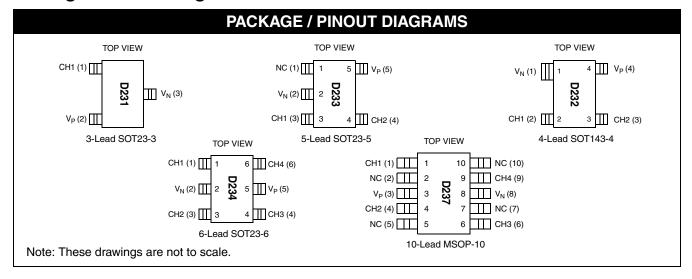
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### **Package / Pinout Diagrams**



## **Pin Descriptions**

	1-CHANNEL, 3-LEAD SOT23-3 PACKAGE					
PIN	NAME	TYPE	DESCRIPTION			
1	CH1	I/O	ESD Channel			
2	$V_{P}$	PWR	Positive voltage supply rail			
3	V <sub>N</sub>	GND	Negative voltage supply rail			
	2-CI	HANNEL, 4-LI	EAD SOT143-4 PACKAGE			
PIN	NAME	TYPE	DESCRIPTION			
1	$V_N$	GND	Negative voltage supply rail			
2	CH1	I/O	ESD Channel			
3	CH2	I/O	ESD Channel			
4	$V_{P}$	PWR	Positive voltage supply rail			
			EAD SOT23-5 PACKAGE			
PIN	NAME	TYPE	DESCRIPTION			
1	NC		No Connect			
2	$V_N$	GND	Negative voltage supply rail			
3	CH1	I/O	ESD Channel			
4	CH2	I/O	ESD Channel			
5	$V_{P}$	PWR	Positive voltage supply rail			

V <sub>N</sub> CH2 CH3 V <sub>P</sub> CH4  HANNEL	TYPE	Negative voltage supply rail ESD Channel ESD Channel Positive voltage supply rail ESD Channel  SOP-10 PACKAGE DESCRIPTION
CH3 V <sub>P</sub> CH4 HANNEL IAME	I/O PWR I/O L, 10-LEAD MS TYPE	ESD Channel Positive voltage supply rail ESD Channel  SOP-10 PACKAGE DESCRIPTION
V <sub>P</sub> CH4 HANNEL	PWR I/O L, 10-LEAD MS TYPE	Positive voltage supply rail ESD Channel  SOP-10 PACKAGE DESCRIPTION
CH4 HANNEL	I/O _, 10-LEAD MS TYPE	ESD Channel  SOP-10 PACKAGE  DESCRIPTION
HANNEI IAME	_, 10-LEAD MS	SOP-10 PACKAGE DESCRIPTION
IAME	TYPE	DESCRIPTION
IAME	TYPE	DESCRIPTION
CH1	1/0	
	I/O	ESD Channel
NC		No Connect
$V_P$	PWR	Positive voltage supply rail
CH2	I/O	ESD Channel
NC		No Connect
CH3	I/O	ESD Channel
NC		No Connect
$V_N$	GND	Negative voltage supply rail
CH4	I/O	ESD Channel
NC		No Connect
(	V <sub>P</sub> CH2 NC CH3 NC V <sub>N</sub>	VP         PWR           CH2         I/O           NC         I/O           CH3         I/O           NC         VN           GND         CH4           I/O         I/O

4-CHANNEL, 6-LEAD SOT23-6 PACKAGES

DESCRIPTION

## **Ordering Information**

PART NUMBERING INFORMATION						
	Lead-free Finish					
# of Channels	Leads	Package	Ordering Part Number <sup>1</sup>	Part Marking		
1	3	SOT23-3	CM1213A-01SO <sup>2</sup>	D231		
2	4	SOT143-4	CM1213A-02SR <sup>2</sup>	D232		
2	5	SOT23-5	CM1213A-02SO <sup>2</sup>	D233		
4	6	SOT23-6	CM1213A-04SO	D234		
4	10	MSOP-10	CM1213A-04MR	D237		

Note 1: Parts are shipped in Tape & Reel form unless otherwise specified.

Note 2: Available Q2 '07.

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# california micro devices

## **Specifications**

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	RATING	UNITS			
Operating Supply Voltage (V <sub>P</sub> - V <sub>N</sub> )	6.0	V			
Operating Temperature Range	-40 to +85	°C			
Storage Temperature Range	-65 to +150	°C			
DC Voltage at any channel input	(V <sub>N</sub> - 0.5) to (V <sub>P</sub> + 0.5)	V			

STANDARD OPERATING CONDITIONS						
PARAMETER	RATING	UNITS				
Operating Temperature Range	-40 to +85	°C				
Package Power Rating SOT23-3, SOT143-4,SOT23-5 and SOT23-6 Packages	225	mW				
MSOP-10 Package	400	mW				

	ELECTRICAL OPERATING CHARACTERISTICS(SEE NOTE 1)						
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V <sub>P</sub>	Operating Supply Voltage (V <sub>P</sub> -V <sub>N</sub> )			3.3	5.5	V	
I <sub>P</sub>	Operating Supply Current	$(V_P - V_N) = 3.3V$			8.0	μΑ	
V <sub>F</sub>	Diode Forward Voltage Top Diode Bottom Diode	I <sub>F</sub> = 8mA; T <sub>A</sub> =25°C	0.60 0.60	0.80 0.80	0.95 0.95	V	
I <sub>LEAK</sub>	Channel Leakage Current	T <sub>A</sub> =25°C; V <sub>P</sub> =5V, V <sub>N</sub> =0V		±0.1	±1.0	μΑ	
C <sub>IN</sub>	Channel Input Capacitance	At 1 MHz, V <sub>P</sub> =3.3V, V <sub>N</sub> =0V, V <sub>IN</sub> =1.65V; Note 2 applies		0.85	1.2	pF	
$\Delta c_{IN}$	Channel Input Capacitance Matching	At 1 MHz, V <sub>P</sub> =3.3V, V <sub>N</sub> =0V, V <sub>IN</sub> =1.65V; Note 2 applies		0.02		pF	
C <sub>MUTUAL</sub>	Mutual Capacitance between signal pin and adjacent signal pin	At 1 MHz, V <sub>P</sub> =3.3V, V <sub>N</sub> =0V, V <sub>IN</sub> =1.65V; Note 2 applies		0.11		pF	
V <sub>ESD</sub>	esd Protection - Peak Discharge Voltage at any channel input, in system a) Contact discharge per IEC 61000-4-2 standard b) Human Body Model, MIL-STD-883,	Notes 2, 4 & 5; T <sub>A</sub> =25°C	±8			kV	
	Method 3015	Notes 2, 3 & 5; T <sub>A</sub> =25°C	±15			kV	
V <sub>CL</sub>	Channel Clamp Voltage Positive Transients Negative Transients	$T_A$ =25°C, $I_{PP}$ = 1A, $t_P$ = 8/20 $\mu$ S; Notes 2, & 5		+9.96 -1.6		V	
R <sub>DYN</sub>	Dynamic Resistance Positive Transients Negative Transients	$I_{PP}=1A$ , $t_P=8/20\mu S$ Any I/O pin to Ground; Note 2 and 5		0.96 0.5		Ω	

Note 1: All parameters specified at  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$  unless otherwise noted.

Note 2: These parameters guaranteed by design and characterization.

Note 3: Human Body Model per MIL-STD-883, Method 3015,  $C_{Discharge} = 100 pF$ ,  $R_{Discharge} = 1.5 K\Omega$ ,  $V_P = 3.3 V$ ,  $V_N$  grounded.

Note 4: Standard IEC 61000-4-2 with  $C_{Discharge} = 150 pF$ ,  $R_{Discharge} = 330 \Omega$ ,  $V_P = 3.3 V$ ,  $V_N$  grounded.

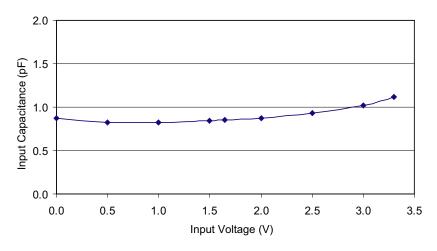
Note 5: These measurements performed with no external capacitor on V<sub>P</sub> (V<sub>P</sub> floating).

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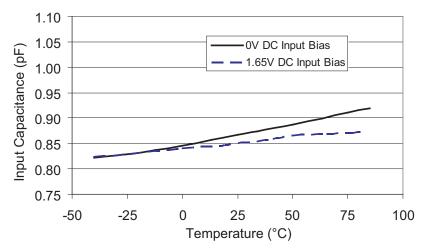
### **Performance Information**

### **Input Channel Capacitance Performance Curves**



### Typical Variation of C<sub>IN</sub> vs. V<sub>IN</sub>

(f=1MHz,  $V_P$  = 3.3V,  $V_N$  = 0V, 0.1  $\mu F$  chip capacitor between  $V_P$  and  $V_{N_c}$  25°C)



Typical Variation of C<sub>IN</sub> vs. Temp

(f=1MHz,  $V_{IN}$ =30mV,  $V_P$  = 3.3V,  $V_N$  = 0V, 0.1  $\mu$ F chip capacitor between  $V_P$  and  $V_N$ )

4



## Performance Information (cont'd)

Typical Filter Performance (nominal conditions unless specified otherwise, 50 Ohm Environment)

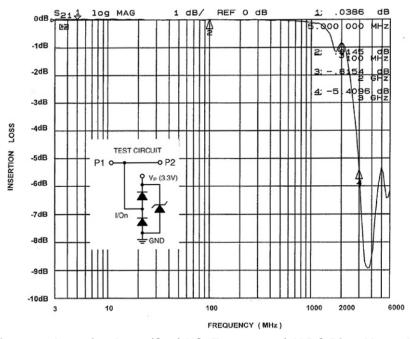


Figure 1. Insertion Loss (S21) VS. Frequency (0V DC Bias, V<sub>P</sub>=3.3V)

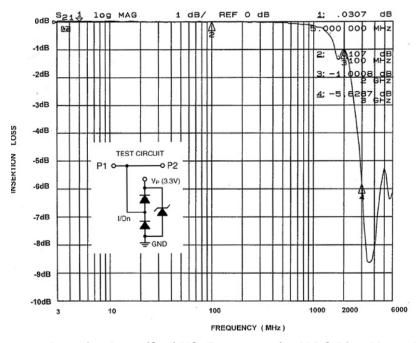


Figure 2. Insertion Loss (S21) VS. Frequency (2.5V DC Bias, V<sub>P</sub>=3.3V)

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### **Application Information**

### **Design Considerations**

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/ Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Figure 3, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to the power supply is represented by  $L_1$  and  $L_2$ . The voltage  $V_{CL}$  on the line being protected is:

$$V_{CL}$$
 = Fwd voltage drop of  $D_1 + V_{SUPPLY} + L_1 \times d(I_{ESD}) / dt$   
+  $L_2 \times d(I_{ESD}) / dt$ 

where  $I_{\text{ESD}}$  is the ESD current pulse, and  $V_{\text{SUPPLY}}$  is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000-4-2 standard results in a current pulse that rises from zero to 30 Amps in 1ns. Here d(I<sub>ESD</sub>)/dt can be approximated by  $\Delta I_{ESD}/\Delta t,$  or 30/(1x10<sup>-9</sup>). So just 10nH of series inductance (L<sub>1</sub> and L<sub>2</sub> combined) will lead to a 300V increment in V<sub>CL</sub>!

Similarly for negative ESD pulses, parasitic series inductance from the  $V_N$  pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

The CM1213A has an integrated Zener diode between  $V_P$  and  $V_N$ . This greatly reduces the effect of supply rail

inductance  $L_2$  on  $V_{CL}$  by clamping  $V_P$  at the breakdown voltage of the Zener diode. However, for the lowest possible  $V_{CL}$ , especially when  $V_P$  is biased at a voltage significantly below the Zener breakdown voltage, it is recommended that a  $0.22\mu F$  ceramic chip capacitor be connected between  $V_P$  and the ground plane.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the  $V_P$  pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

#### Additional Information

See also California Micro Devices Application Note AP209, "Design Considerations for ESD Protection," in the Applications section at www.calmicro.com.

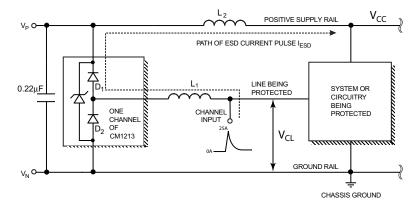


Figure 3. Application of Positive ESD Pulse between Input Channel and Ground





### **Mechanical Details**

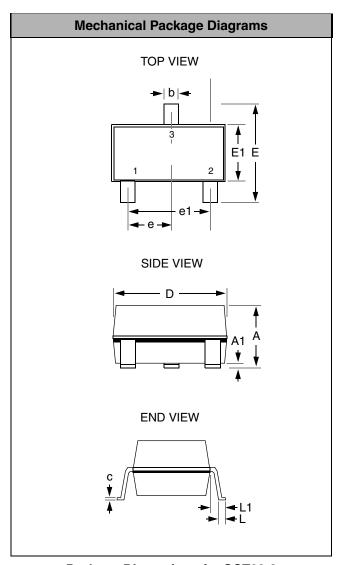
The CM1213A is available in SOT23-3, SOT143-4, SOT23-5, SOT23-6, and MSOP-10 packages with a lead-free finishing option. The various package drawings are presented below.

#### SOT23-3 Mechanical Specifications, 3 pin

The CM1213A is supplied in a 3-pin SOT23 package. Dimensions are presented below.

For complete information on the SOT23-3, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS						
Package	SOT2	3-3 (JEDEC	C name is T	O-236)		
JEDEC No.		TO-236	(Var. AB)			
Pins/Leads			3			
Dimensions	Millimeters		Inches			
Difficusions	Min	Max	Min	Max		
Α	0.89	1.12	0.0350	0.0441		
A1	0.01	0.10	0.0004	0.0039		
b	0.30	0.50	0.0118	0.0197		
С	0.08	0.20	0.0031	0.0079		
D	2.80	3.04	0.1102	0.1197		
Е	2.10	2.64	0.0827 0.103			
E1	1.20	1.40	0.0472	0.0551		
е	0.95	BSC	0.037	4 BSC		
e1	1.90	BSC	0.074	8 BSC		
L	0.40	0.60	0.0157	0.0236		
L1	0.54 REF 0.0213 REF					
# per tape and reel	3000 pieces					
Controlling dimension: millimeters						



Package Dimensions for SOT23-3



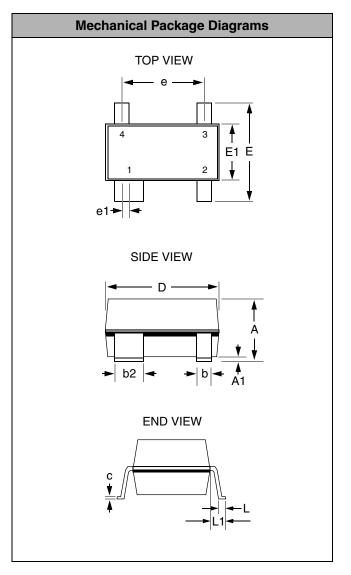


### SOT143 Mechanical Specifications, 4 pin

The CM1213A is packaged in a 4-pin SOT143 package. Dimensions are presented below.

For complete information on the SOT143 package, see the California Micro Devices SOT143 Package Information document.

PACKAGE DIMENSIONS						
Package		SO	Γ143			
Pins			4			
Dimensions	Millimeters		Inches			
Difficusions	Min	Max	Min	Max		
Α	0.80	1.22	0.031	0.048		
A1	0.05	0.15	0.002	0.006		
b	0.30	0.50	0.012	0.019		
b2	0.76	0.89	0.030	0.035		
С	0.08	0.20	0.003	0.008		
D	2.80	3.04	0.110	0.119		
E	2.10	2.64	0.082	0.103		
E1	1.20	1.40	0.047	0.055		
е	1.92	BSC	0.07	5 BSC		
e1	0.20	) BSC	0.008	B BSC		
L	0.4	0.6	0.016	0.024		
L1	0.54 REF 0.021 REF					
# per tape and reel	3000 pieces					
Controlling dimension: millimeters						



Package Dimensions for SOT143.

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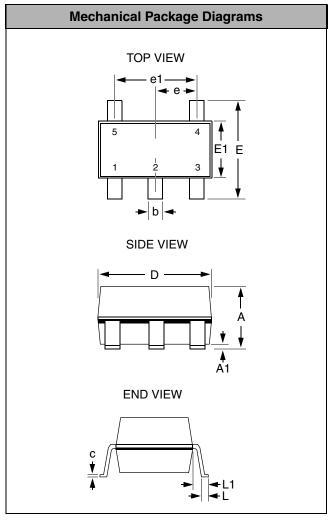


### SOT23-5 Mechanical Specifications, 5 pin

The CM1213A is supplied in a 5-pin SOT23 package. Dimensions are presented below.

For complete information on the SOT23-5, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS						
Package		SOT	23-5			
JEDEC No.		MO-178	(Var. AA)			
Pins/Leads			5			
Dimensions	Millim	neters	Inches			
Difficusions	Min	Max	Min	Max		
Α		1.45		0.0571		
A1	0.00	0.15	0.0000	0.0059		
b	0.30	0.50	0.0118	0.0197		
С	0.08	0.22	0.0031	0.0087		
D	2.75	3.05	0.1083	0.1201		
E	2.60	3.00	0.1024 0.118			
E1	1.45	1.75	0.0571	0.0689		
е	0.95	BSC	0.037	4 BSC		
e1	1.90	) BSC	0.074	8 BSC		
L	0.30	0.60	0.0118	0.0236		
L1	0.60 REF 0.0236 REF					
# per tape and reel	3000 pieces					
Controlling dimensions: millimeters						



Package Dimensions for SOT23-5.

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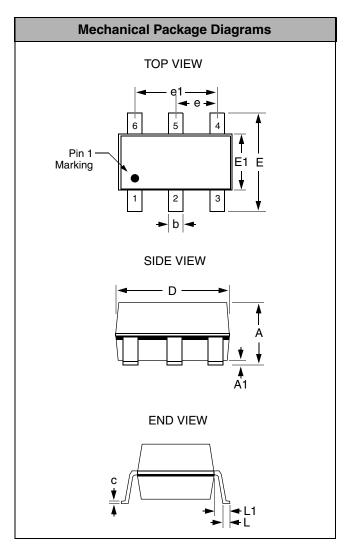


### SOT23-6 Mechanical Specifications, 6 pin

The CM1213A is supplied in a 6-pin SOT23 package. Dimensions are presented below.

For complete information on the SOT23-6, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS						
Package		SOT	Г23-6			
JEDEC No.		MO-178	(Var. AB)			
Pins/Leads			6			
Dimensions	Millim	neters	Inches			
Difficusions	Min	Max	Min	Max		
Α		1.45		0.0571		
A1	0.00	0.15	0.0000	0.0059		
b	0.30	0.50	0.0118	0.0197		
С	0.08	0.22	0.0031	0.0087		
D	2.75	3.05	0.1083	0.1201		
E	2.60	3.00	0.1024	0.1181		
E1	1.45	1.75	0.0571	0.0689		
е	0.95	BSC	0.037	4 BSC		
e1	1.90	BSC	0.074	8 BSC		
L	0.30	0.60	0.0118	0.0236		
L1	0.60 REF 0.0236REF					
# per tape and reel	3000 pieces					
Controlling dimension: millimeters						



Package Dimensions for SOT23-6.



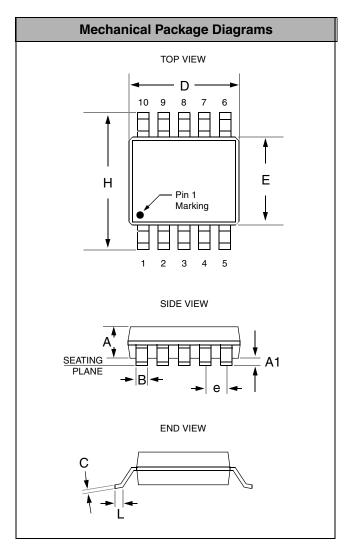


### MSOP-10 Mechanical Specifications, 10 pin

The CM1213A is supplied in a 10-pin MSOP. Dimensions are presented below.

For complete information on the MSOP-10, see the California Micro Devices MSOP Package Information document.

PACKAGE DIMENSIONS						
Package		MS	SOP			
Pins		1	10			
Dimensions	Millim	neters	Inches			
Difficusions	Min	Max	Min	Max		
Α	0.75	0.95	0.028	0.038		
A1	0.05	0.15	0.002	0.006		
В	0.17	0.27	0.007	0.013		
С	0.13	0.23	0.005	0.009		
D	2.90	3.10	0.114	0.122		
E	2.90	3.10	0.114	0.122		
е	0.50	BSC	0.019	6 BSC		
Н	4.90 BSC 0.193 BSC					
L	0.40	0.70	0.0137	0.029		
# per tape and reel	4000					
Controlling dimension: millimeters						



**Package Dimensions for MSOP-10**